40V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET
PowerDI3333-8

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_C = +25°C
40V	13.7mΩ @ V_{GS} = 10V	49.8A
	26mΩ @ V_{GS} = 4.5V	36.7A

Features and Benefits

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- Low $R_{DS(ON)}$ – Ensures On State Losses are Minimized
- Excellent Q_{gd} x $R_{DS(ON)}$ Product (FOM)
- Wettable Flank for Improved Optical Inspection
- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Description and Applications

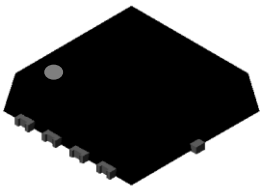
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

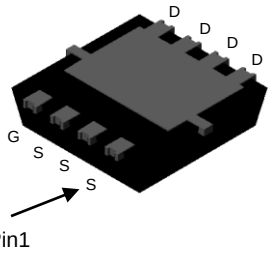
Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish - Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.072 grams (Approximate)

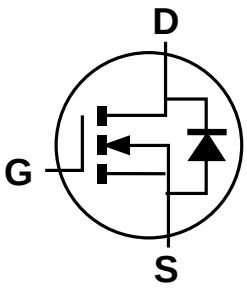
PowerDI3333-8 (SWP) (Type UX)



Top View



Bottom View



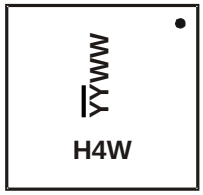
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH4014LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMTH4014LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



H4W = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 20 = 2020)
WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.

Maximum Ratings (@T_A =+ 25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6), V_{GS} = 10V	T_C = +25°C T_C = +100°C	I_D	49.8 35.2	A
Continuous Drain Current (Note 5), V_{GS} = 10V	T_A = +25°C T_A = +100°C	I_D	11.5 8.1	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	180	A
Maximum Continuous Body Diode Forward Current (Note 6)		I_S	45	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)		I_{SM}	180	A
Avalanche Current, L=0.1mH		I_{AS}	19.8	A
Avalanche Energy, L=0.1mH		E_{AS}	19.6	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	3.1	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	48.6	°C/W
Total Power Dissipation (Note 6)	T_C = +25°C	P_D	57.7	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	2.5	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	40	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 32V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	1	—	3	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	9.8	13.7	mΩ	V_{GS} = 10V, I_D = 20A
		—	14.5	26		V_{GS} = 4.5V, I_D = 10A
Diode Forward Voltage	V_{SD}	—	0.9	1.2	V	V_{GS} = 0V, I_S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	750	—	pF	V_{DS} = 20V, V_{GS} = 0V, f = 1MHz
Output Capacitance	C_{oss}	—	225	—		
Reverse Transfer Capacitance	C_{rss}	—	21	—		
Gate Resistance	R_g	—	1.1	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	5.7	—	nC	V_{DS} = 20V, I_D = 20A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	11.2	—		
Gate-Source Charge	Q_{gs}	—	2.0	—		
Gate-Drain Charge	Q_{gd}	—	2.2	—		
Turn-On Delay Time	$t_{D(ON)}$	—	3.5	—	ns	V_{DD} = 20V, V_{GS} = 10V, R_g = 1.6Ω, I_D = 20A
Turn-On Rise Time	t_R	—	4.6	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	12.4	—		
Turn-Off Fall Time	t_F	—	4.9	—		
Body Diode Reverse Recovery Time	t_{RR}	—	11.3	—	ns	I_F = 15A, di/dt = 400A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	9.5	—	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.

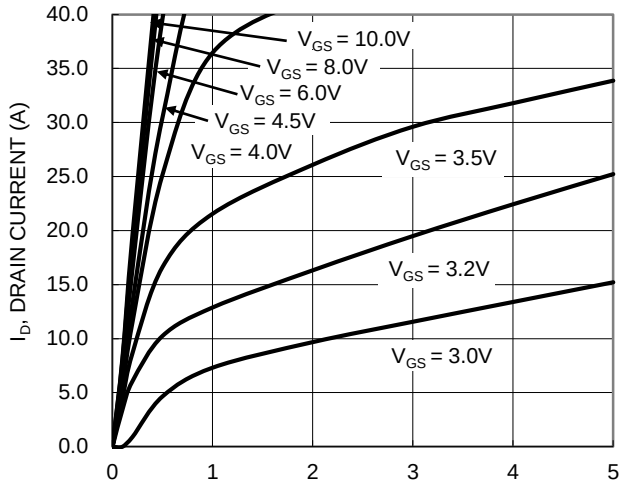


Figure 1. Typical Output Characteristic

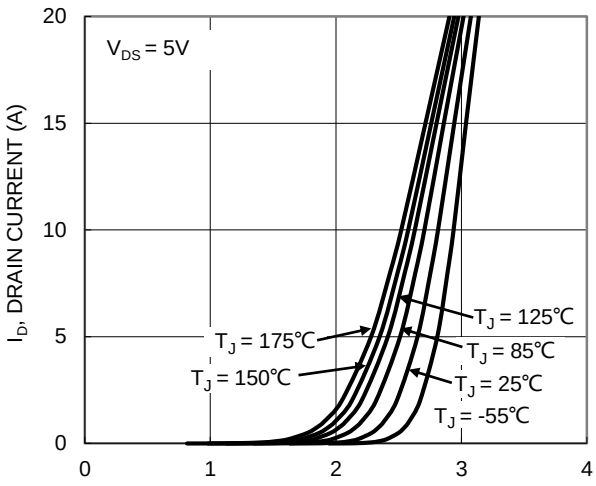


Figure 2. Typical Transfer Characteristic

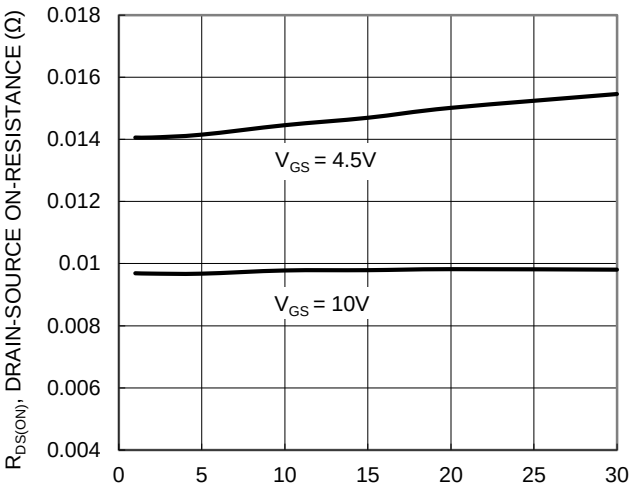


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

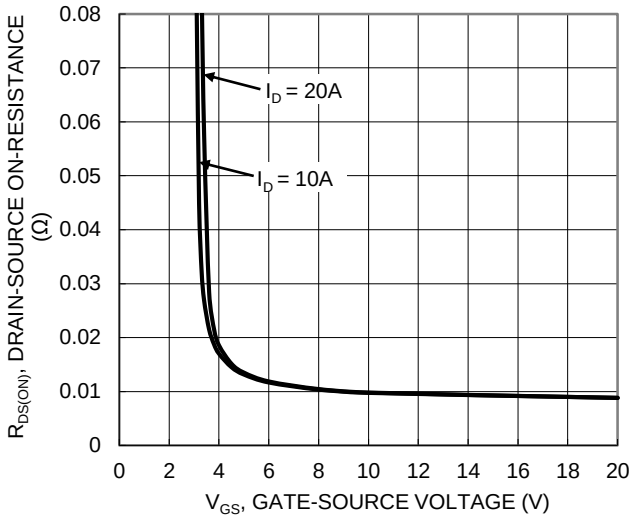


Figure 4. Typical Transfer Characteristic

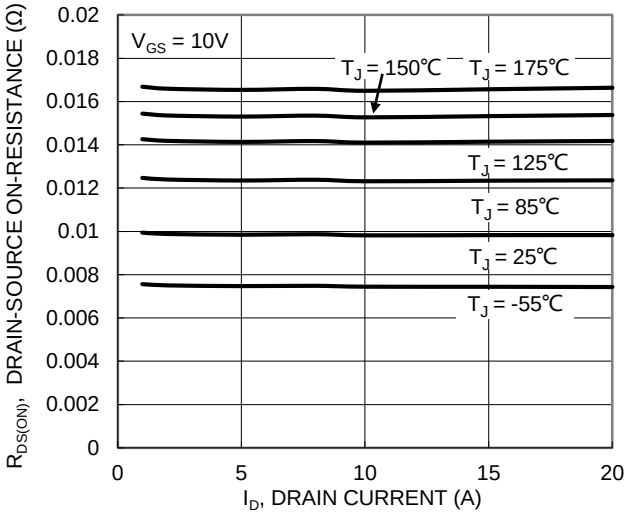


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

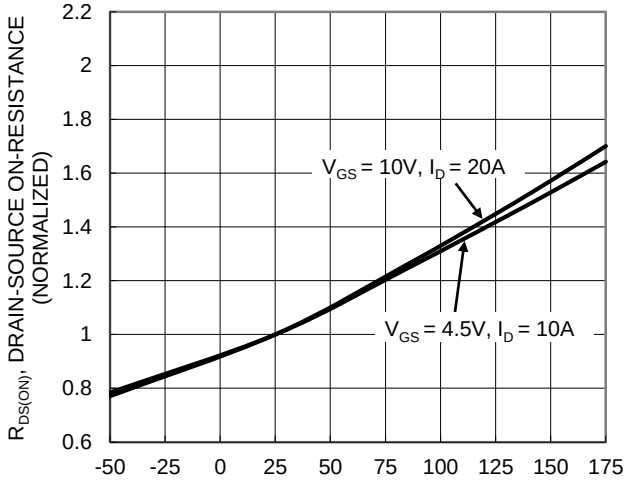


Figure 6. On-Resistance Variation with Junction Temperature

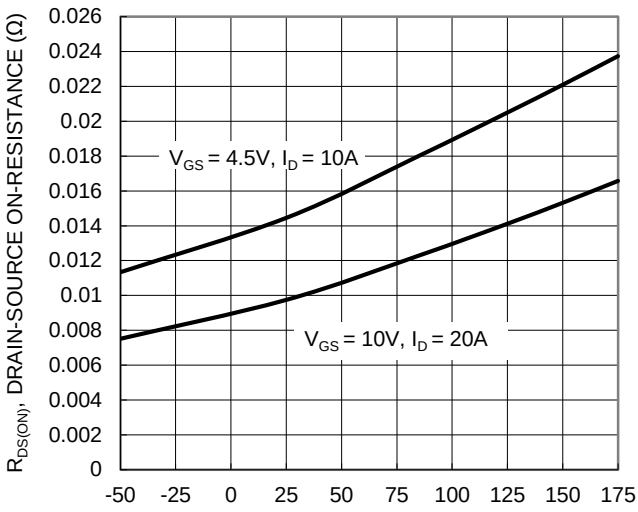


Figure 7. On-Resistance Variation with Junction Temperature

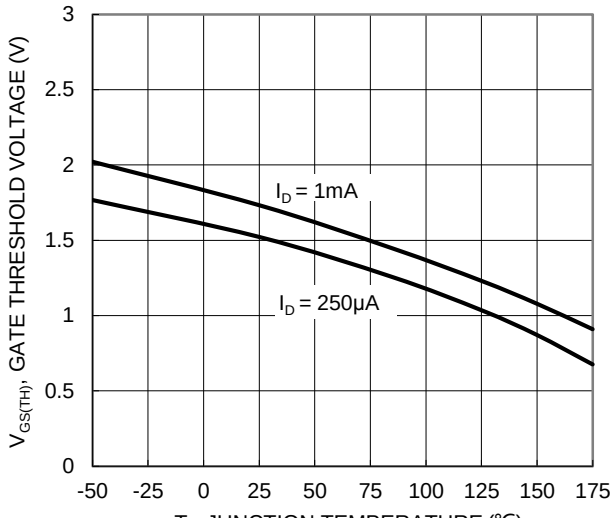


Figure 8. Gate Threshold Variation vs. Junction Temperature

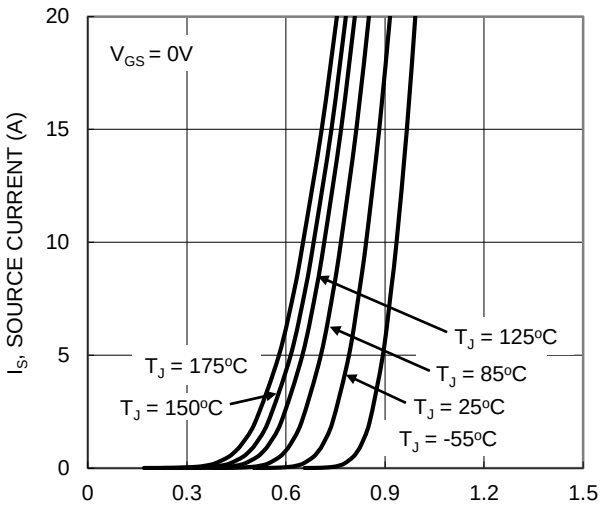


Figure 9. Diode Forward Voltage vs. Current

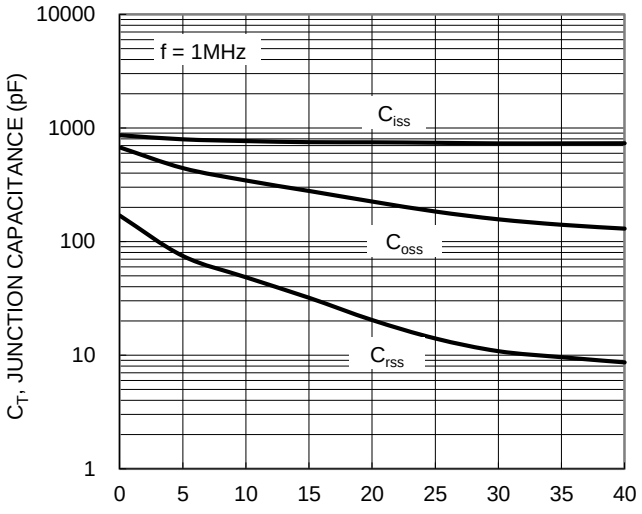


Figure 10. Typical Junction Capacitance

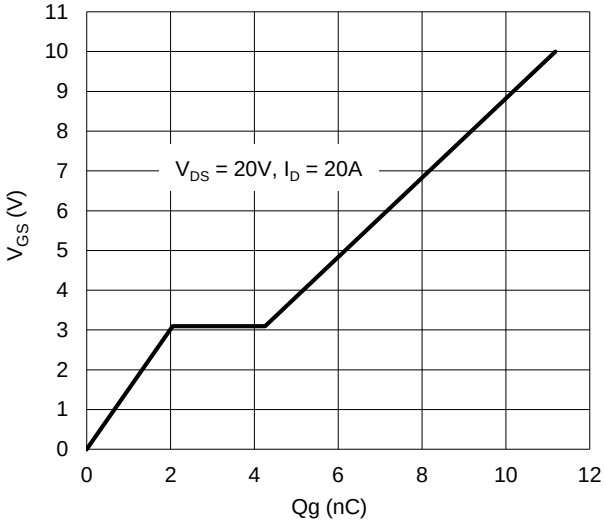


Figure 11. Gate Charge

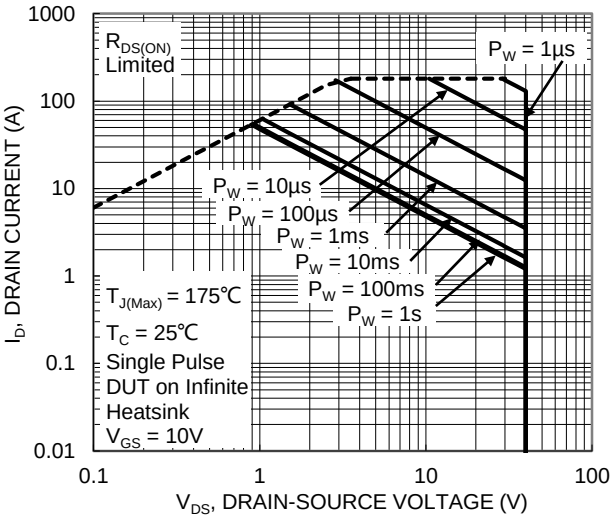


Figure 12. SOA, Safe Operation Area

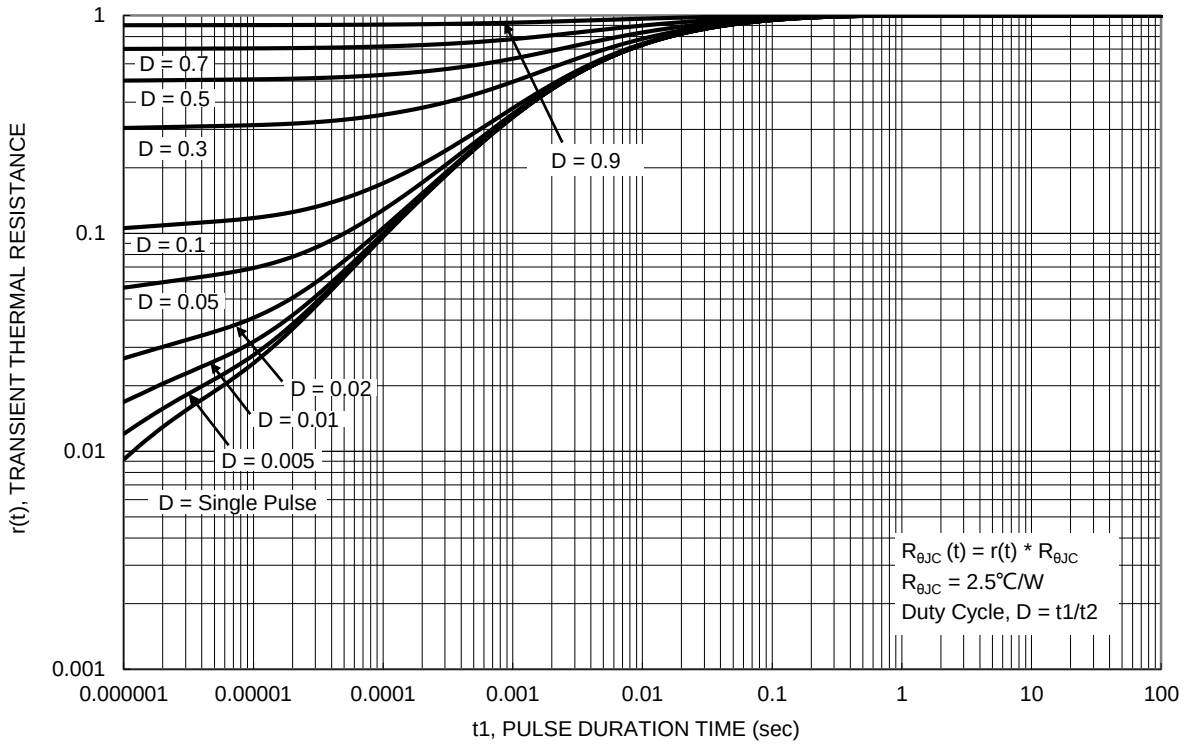
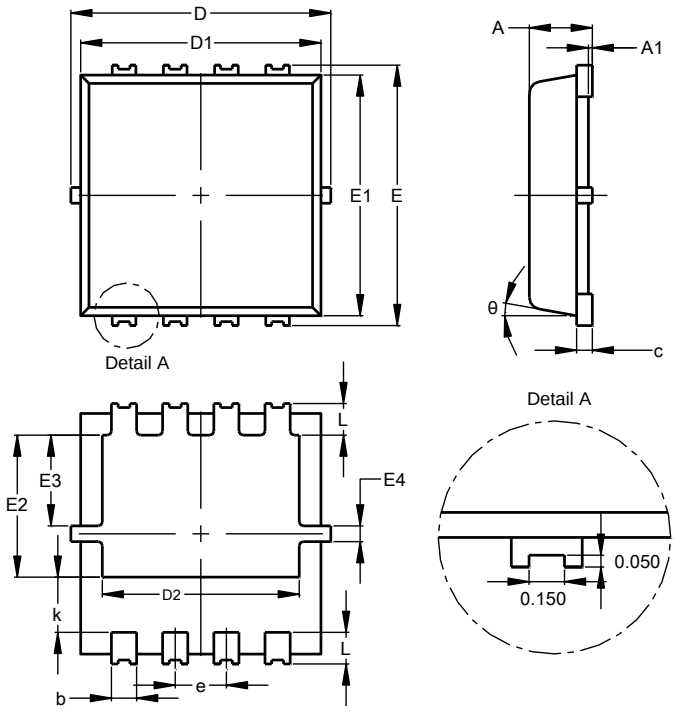


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

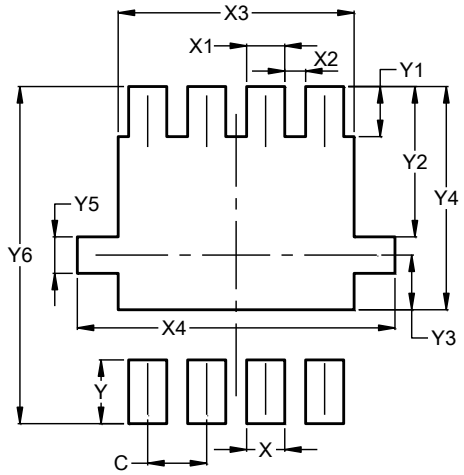


PowerDI3333-8 (SWP) (Type UX)			
Dim	**Min**	**Max**	**Typ**
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	–	–	0.65
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

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